



## ITC1000

### 1000 WATT, 50V, Pulsed Avionics 1030 MHz

#### GENERAL DESCRIPTION

The **ITC1000** is a common base bipolar transistor. It is designed for pulsed interrogator systems in the frequency band of 1030 MHz. The device has gold thin-film metallization for proven high MTTF. The transistor includes input returns for improved output rise time. Low thermal resistance package reduces junction temperature which extends the life time of the product.

#### ABSOLUTE MAXIMUM RATINGS

##### Power Dissipation

Device Dissipation<sup>1</sup> @25°C (P<sub>d</sub>) 3400 W  
Thermal Resistance<sup>1</sup> (θ<sub>JC</sub>) .08°C/W

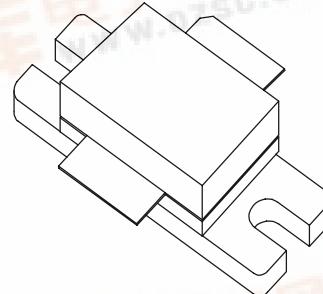
##### Voltage and Current

Collector-Base Voltage 65V  
Emitter-Base Voltage 3.5V  
Collector Current<sup>1</sup> 80A

##### Temperatures

Storage Temperature -40 to +150°C  
Operating Junction Temperature<sup>1</sup> +200°C

#### CASE OUTLINE 55SW, Style 1 Common Base



#### ELECTRICAL CHARACTERISTICS @ 25°C

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
BVebo <sup>2</sup>	Emitter-Base Breakdown(open)	Ie=50mA	3.5			V
BVces	Collector-Emitter Breakdown(shorted)	Ic=30mA	65			V
BVceo <sup>2</sup>	Collector-Emitter Breakdown (open)	Ic=30mA	30			V
h <sub>FE</sub> <sup>2</sup>	DC Current Gain	Ic=5A, Vce=5V	20	45	80	β

#### FUNCTIONAL CHARACTERISTICS @ 25°C

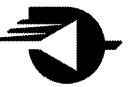
G <sub>PB</sub>	Common Base Power Gain	V <sub>cc</sub> = 50V, F = 1030MHz, P <sub>out</sub> =1000W, PW=1μS, DF=1%	8.0	8.5		dB
η <sub>c</sub>	Collector Efficiency	V <sub>cc</sub> = 50V, F = 1030MHz, P <sub>out</sub> =1000W, PW=1μS, DF=1%	35	45		%
t <sub>r</sub>	Rise Time	V <sub>cc</sub> = 50V, F = 1030MHz, P <sub>out</sub> =1000W, PW=1μS, DF=1%		50	80	nS
VSWR	Output Load Mismatch	V <sub>cc</sub> = 50V, F = 1030MHz, P <sub>out</sub> =1000W, PW=1μS, DF=1%			4:1	Ψ
Z <sub>in</sub>	Series Input Impedance (Circuit source impedance @ test cond.)	V <sub>cc</sub> = 50V, F = 1030MHz, P <sub>out</sub> =1000W, PW=1μS, DF=1%			1.0-j2.0	Ω
Z <sub>out</sub>	Series Output Impedance (Circuit load impedance @ test cond.)	V <sub>cc</sub> = 50V, F = 1030MHz, P <sub>out</sub> =1000W, PW=1μS, DF=1%			0.6-j2.1	Ω

<sup>1</sup> At rated output power and pulse conditions

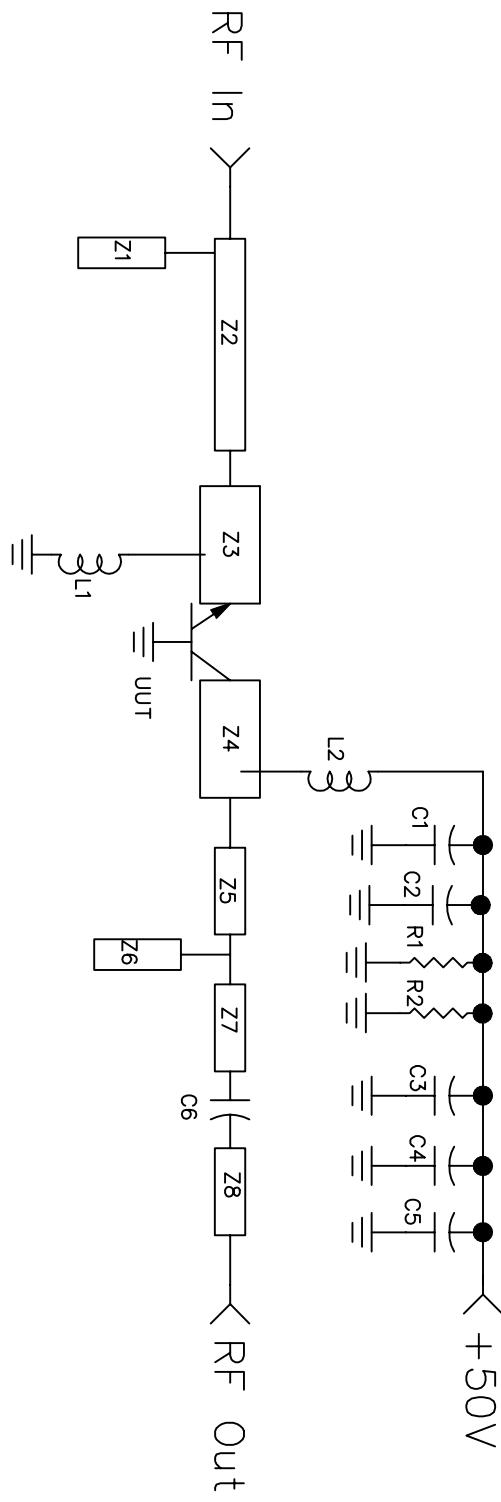
<sup>2</sup> Contains input returns and cannot be measured

Initial Issue May 1999





# Test Fixture Schematic For The ITC1000



Z1 – Z8 See PCB Autocad Drawing ITC1000pcb\_rev4.dwg

L1 1/2 Turn 18 Awg, .335 ID, 1.4" long  
L1 0.100" x 0.150" x 0 .005" copper strip

C1 30pF ATC 100B  
C2 62pF ATC 100B  
C3 1000 uF, 63V  
C4 470 uF, 63V  
C5 330 uF, 63V  
C6 56 pF, ATC100B  
R1, R2 10K, 1/4W, 1206

MECHANICAL DWG OF FIXTURE LAYOUT AVAILABLE UPON REQUEST

ZONE	REV	DESCRIPTION	DATE	APPROVED
		ITC1000 Test Fixture Schematic	OPJR2	SCALE n/a SHEET